

1) Oxidation

Time (sec)	
Temp (C)	

Anneal

Time (sec)	
Temp (C)	

2) Measurements after Process Completion:

Gate Oxide Thickness (Nanospec):

ACTV Sheet Resistivity (Control Wafer):

Questions (In preparation for Lab Report 1):

Calculate Theoretical Oxide Thickness using Deal-Grove Model

Calculate surface dopant concentration from the sheet resistance.